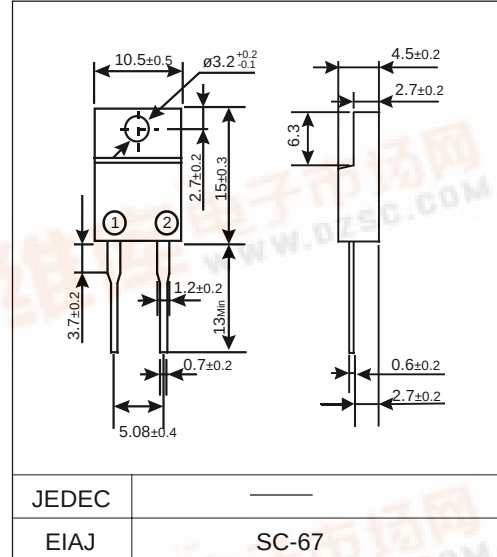


YG812S04R (10A)

(45V / 10A)

SCHOTTKY BARRIER DIODE

■ Outline drawings, mm



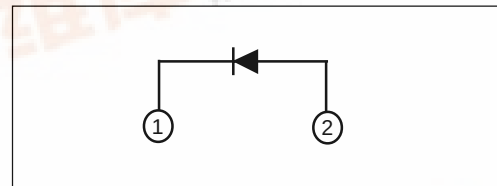
■ Features

- Insulated package by fully molding
- Low V_F
- Super high speed switching
- High reliability by planer design

■ Applications

- High speed power switching

■ Connection diagram



■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		45	V
Non-repetitive peak reverse voltage	V_{RSM}	$t_w=500ns$, duty=1/40	48	V
Isolating voltage	Viso	Terminals to Case, AC, 1min.	1500	V
Average output current	I_o	Square wave, duty=1/2 $T_c=124^{\circ}C$	10	A
Surge current	I_{FSM}	Sine wave 10ms	250	A
Operating junction temperature	T_j		-40 to +150	$^{\circ}C$
Storage temperature	T_{slg}		-40 to +150	$^{\circ}C$

- Electrical characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=10A$	0.6	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	2.0	mA

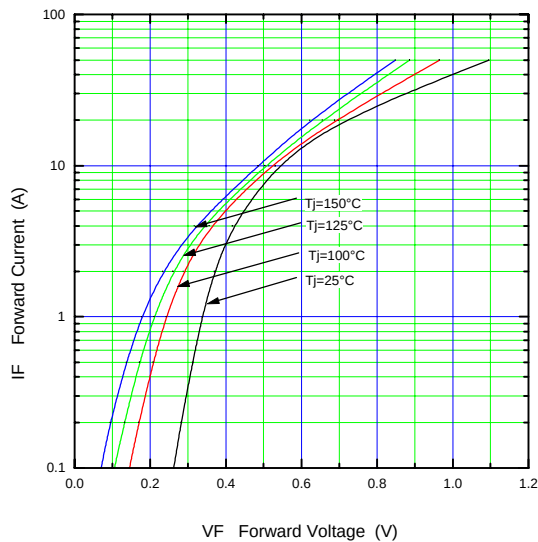


(45V / 10A)

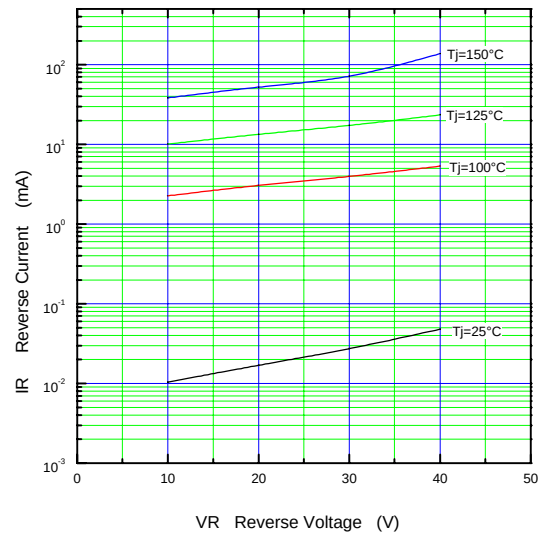
YG812S04R (10A)

Characteristics

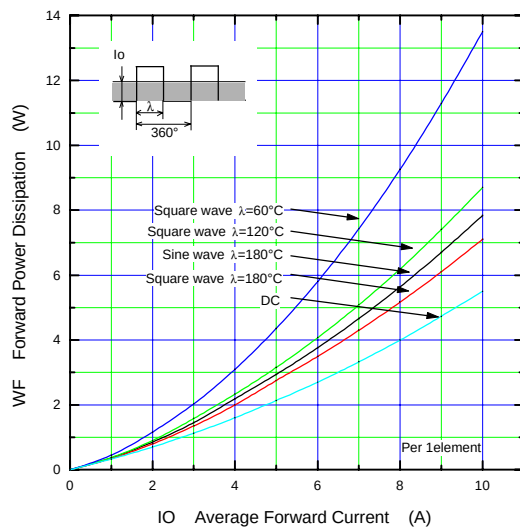
Forward Characteristic (typ.)



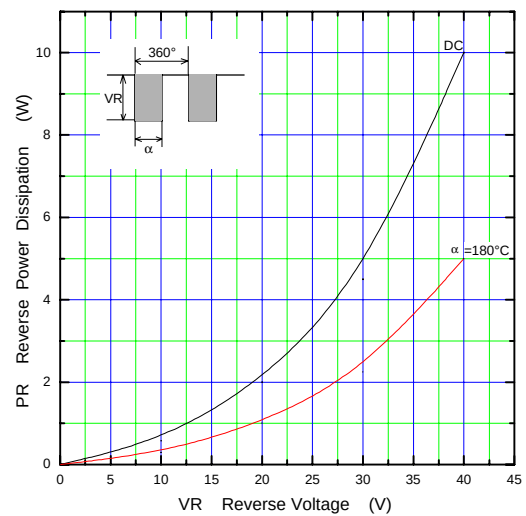
Reverse Characteristic (typ.)



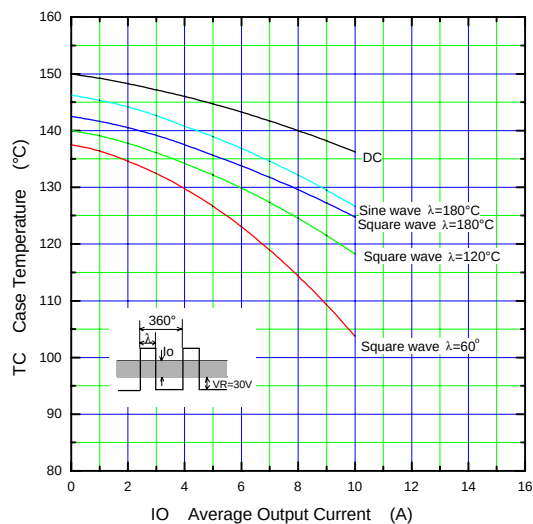
Forward Power Dissipation



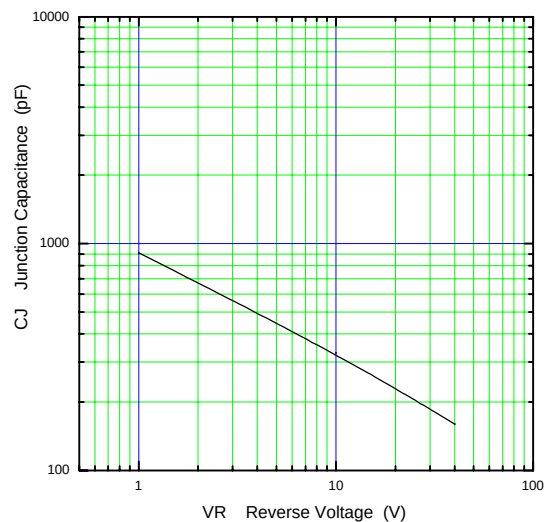
Reverse Power Dissipation



Current Derating (I_O - T_C)



Junction Capacitance Characteristic (typ.)



(45V / 10A)

YG812S04R (10A)

